# RT1N436M-T150

Transistor With Resistor For Switching Application Silicon NPN Epitaxial Type

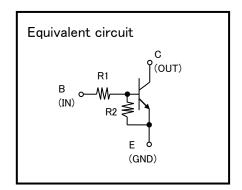
AEC-Q101 Compliance

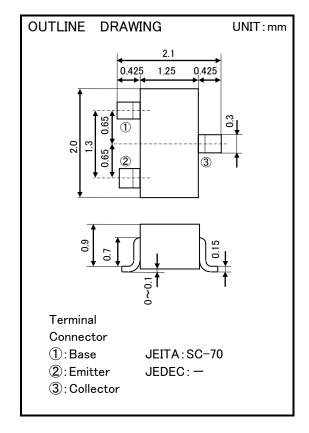
#### **FEATURE**

- Built-in bias resistor (R1=4.7k $\Omega$ ,R2=47k $\Omega$ )
- Mini package for easy mounting

#### **APPLICATION**

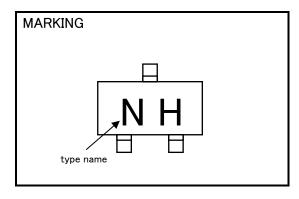
Inverted circuit, switching circuit, interface circuit, driver circuit.





## MAXIMUM RATING(Ta=25°C)

| SYMBOL           | PARAMETER                    | RATING            | UNIT |  |
|------------------|------------------------------|-------------------|------|--|
| $V_{CBO}$        | Collector to Base voltage    | 50                | ٧    |  |
| $V_{EBO}$        | Emitter to Base voltage      | 6                 | V    |  |
| $V_{CEO}$        | Collector to Emitter voltage | 50                | V    |  |
| $V_{IN}$         | Input voltage                | 30                | V    |  |
| $\mathbf{I}_{C}$ | Collector current            | 100               | mA   |  |
| $I_{CM}$         | Peak Collector current       | 200               | mA   |  |
| Pc               | Collector dissipation        | 200               | mW   |  |
| $T_{j}$          | Junction temperature         | +150              | °C   |  |
| $T_{stg}$        | Storage temperature          | −55 <b>~</b> +150 | °C   |  |



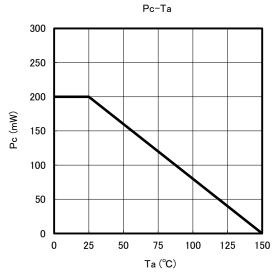
### ELECTRICAL CHARACTERISTICS (Ta=25°C)

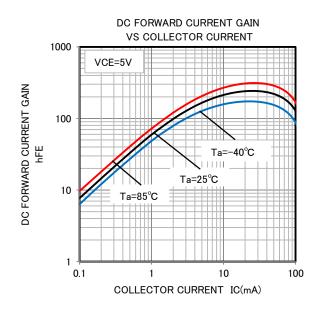
| SYMBOL               | PARAMETER                 | TEST CONDITION                         | LIMIT |     |     | UNIT |
|----------------------|---------------------------|--|-------|-----|-----|------|
|                      |                           |  | MIN   | TYP | MAX | UNIT |
| $V_{(BR)CEO}$        | C to E breakdown voltage  | $I_C=100 \mu A, R_{BE}=\infty$         | 50    | l   | _   | V    |
| $\mathbf{I}_{CBO}$   | Collector cut off current | $V_{CB}=50V$ , $I_{E}=0$               | _     | l   | 0.1 | μΑ   |
| $\mathbf{I}_{EBO}$   | Emitter cut off current   | $V_{EB}=5V$ , $I_{C}=0$                | 73    | 97  | 140 | μΑ   |
| $h_{FE}$             | DC forward current gain   | $V_{CE}=5V$ , $I_{C}=10mA$             | 80    | l   | _   | _    |
| $V_{\text{CE(sat)}}$ | C to E saturation voltage | $I_C=10$ mA, $I_B=0.5$ mA              | _     | l   | 0.3 | V    |
| $V_{I(ON)}$          | Input on voltage          | $V_{CE}$ =0.2 $V$ , $I_{C}$ =5 $mA$    | _     | 0.8 | 1.4 | V    |
| $V_{I(OFF)}$         | Input off voltage         | $V_{CE}$ =5 $V$ , $I_{C}$ =100 $\mu$ A | 0.4   | 0.6 | _   | V    |
| R1                   | Input resistor            | _                                      | 3.3   | 4.7 | 6.1 | kΩ   |
| R2/R1                | Resistor ratio            | _                                      | 8     | 10  | 12  | _    |
| $f_T$                | Gain band width product   | $V_{CE}=6V$ , $I_{E}=-10mA$            | _     | 200 | _   | MHz  |

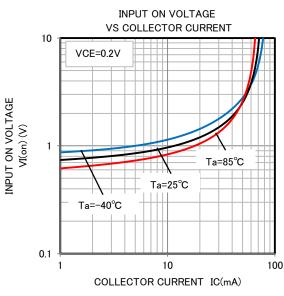
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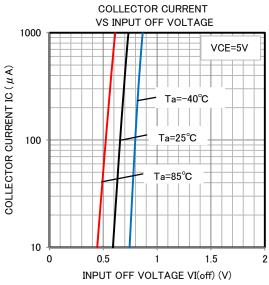
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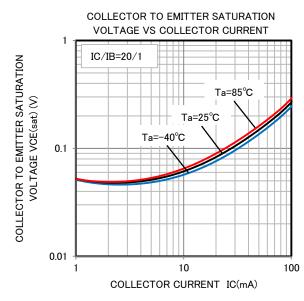












#### Keep safety first in your circuit designs!

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